**1). The electrical conductivity of semiconductor lies in \_\_\_\_\_\_\_\_\_\_\_**

 Inductor

 Conductor

 Both a and b

 None of the above

**2). The semiconductor materials have \_\_\_\_\_\_\_\_**

 Free electrons

 Holes

 Both a and b

 None of the above

**3). By adding pentavalent impurity atoms to an intrinsic semiconductor material, the number of \_\_\_\_\_\_\_\_ increased**

 Free electrons

 Holes

 Both a and b

 None of the above

Hint

**4). \_\_\_\_\_\_\_\_\_\_ is an example of semiconductor**

 Resistors

 Capacitors

 Op-amps

 All of the above

Hint

**5). Based on their conductivity properties the solids are categorized into \_\_\_\_\_\_\_\_**

 One

 Two

 Three

 Four

Hint

**6). The resistivity of the germanium is \_\_\_\_\_\_\_\_\_\_**

 0.46Ωm

 1.0 Ωm

 2.1 Ωm

 3.0 Ωm

Hint

**7). The resistivity of the silicon is \_\_\_\_\_\_\_\_\_\_**

 0.46Ωm

 100Ωm

 210Ωm

 640Ωm

Hint

**8). How many types of semiconductors are there?**

 One

 Two

 Three

 Four

Hint

**9). How many types of extrinsic semiconductors are there?**

 One

 Two

 Three

 Four

Hint

**10). How many outer shell valence electrons does silicon have?**

 One

 Two

 Three

 Four

Hint

**11). The majority charge carriers in a p-type semiconductor is \_\_\_\_\_\_\_\_\_\_**

 Holes

 Electrons

 Both a and b

 None of the above

Hint

**12). Which one is a conductor example?**

 Copper

 Glass

 Both a and b

 None of the above

Hint

**13). \_\_\_\_\_\_\_\_ is an example of acceptor**

 Boron

 Phosphorous

 Copper

 Glass

Hint

**14). The drift current density effected by \_\_\_\_\_\_\_**

 An electric filed

 Concentration gradient in holes

 Concentration gradient in free electrons

 All of the above

Hint

**15). For an intrinsic semiconductor material to have more holes, they are doped with \_\_\_\_\_\_\_\_atoms**

 Trivalent impurity

 Pentavalent impurity

 Both a and b

 None of the above

Hint

**16). How many valence electrons do trivalent impurity atoms have in their valence shell?**

 One

 Two

 Three

 Four

Hint

**17). The majority charge carriers in N-type semiconductor is \_\_\_\_\_\_\_\_\_\_**

 Holes

 Electrons

 Both a and b

 None of the above

Hint

**18). Which one is an insulator example?**

 Glass

 Copper

 Phosphorous

 None of the above

Hint

**19). Which one is a donor example?**

 Boron

 Copper

 Phosphorous

 None of the above

Hint

**20). The diffusion current density effected by \_\_\_\_\_**

 Concentration gradient in the hole

 Concentration gradient in free electrons

 Both a and b

 None of the above

Hint

**21). The semiconductors doped with trivalent atoms are \_\_\_\_\_\_\_\_ type of semiconductor**

 P-type

 N-type

 Both a and b

 None of the above

Hint

**22). The doping process converts intrinsic semiconductor material into extrinsic semiconductor material**

 True

 False

Hint

**23). In P-type semiconductor \_\_\_\_\_\_\_\_ are the majority charge carriers**

 Electrons

 Holes

 Both a and b

 None of the above

Hint

**24). Atoms consists of \_\_\_\_\_\_\_\_**

 Neutrons

 Electrons

 Protons

 All of the above

Hint

**25). The hydrogen atom doesn’t have a \_\_\_\_\_\_\_\_\_\_**

 Neutrons

 Electrons

 Protons

 All of the above

Hint

**Semiconductor Theory Important MCQs**

**26). The difference in energy between conduction and valance band is called the band gap**

 True

 False

Hint

**27). The band gap between conduction and valance band in an insulator is \_\_\_\_\_\_**

 Low

 Very low

 High

 Moderate

Hint

**28). The band gap in a semiconductor is \_\_\_\_\_\_\_ compared to an insulator**

 Big

 Very big

 Smaller

 Very small

Hint

**29). In N-type semiconductor \_\_\_\_\_\_\_\_ are the minority charge carriers**

 Electrons

 Holes

 Both a and b

 None of the above

Hint

**30). In \_\_\_\_\_\_\_ there’s no band gap**

 Conductor

 Insulator

 Both a and b

 None of the above

Hint

**31). The solids have \_\_\_\_\_\_**

 Rigid shape

 Fixed volume

 Fixed shape

 All of the above

Hint

**32). \_\_\_\_\_\_\_\_\_ current happens in the valence band**

 Electron current

 Valance current

 Electron or valance current

 None of the above

Hint

**33). The liquids have \_\_\_\_\_\_\_\_\_**

 Non-rigid shape

 Fixed volume

 No fixed shape

 All of the above

Hint

**34). \_\_\_\_\_\_\_\_\_ current happens in conduction band**

 Electron current

 Valance current

 Electron or valance current

 None of the above

Hint

**35). The gases are \_\_\_\_\_\_\_\_\_\_**

 Non-rigid

 No fixed volume

 No fixed shape

 All of the above

Hint

**36). \_\_\_\_\_\_\_\_ are the crystalline solids**

 Silver

 Gold

 Diamond

 All of the above

Hint

**37). \_\_\_\_\_\_\_\_ is an example of amorphous solid**

 Silver

 Sugar

 Glass

 All of the above

Hint

**38). \_\_\_\_\_\_\_\_ is an example for metal conductor**

 Aluminium

 Copper

 Gold, silver

 All of the above

Hint

Read more about [Conductors](https://www.watelectrical.com/what-are-electrical-conductors-types-and-their-properties/)

**39). An insulators have\_\_\_\_\_\_\_**

 Very high resistivity

 Low conductivity

 High conductivity

 Both a and b

Hint

**40). \_\_\_\_\_\_\_\_\_ is an example for insulator**

 Rubber

 Silver

 Gold

 None of the above

Hint

**41). Nucleus consists \_\_\_\_\_\_**

 Only protons

 Only neutrons

 Both a and b

 None of the above

Hint

**42). \_\_\_\_\_\_\_\_\_\_ is an example of organic semiconductor**

 GaAS

 Polypyrole

 Anthracene

 None of the above

Hint

**43). \_\_\_\_\_\_\_\_\_\_ is an example of inorganic semiconductor**

 GaAS

 Polypyrole

 Anthracene

 None of the above

Hint

**44). \_\_\_\_\_\_\_\_\_\_ is an example of organic polymer**

 GaAS

 Polypyrole

 Anthracene

 None of the above

Hint

**45). The concentration of electrons in P-type semiconductor is \_\_\_\_\_\_\_\_\_\_\_\_\_\_**

 Low

 High

 Very high

 Moderate

Hint

**46). In which semiconductor the energy gap is small?**

 Intrinsic

 Extrinsic

 Both a and b

 None of the above

Hint

**47). In which semiconductor the conductivity is low?**

 Intrinsic

 Extrinsic

 Both a and b

 None of the above

Hint

**48). Intrinsic semiconductor has\_\_\_\_\_\_\_\_at room temperature**

 Few free electrons

 Few holes

 Both a and b

 None of the above

Hint

**49). Intrinsic semiconductor has\_\_\_\_\_\_\_\_at absolute temperature**

 No free electrons

 No holes

 Both a and b

 None of the above

Hint

**50).How many valence electrons do pentavalent impurities have?**

 One

 Two

 Three

 Five

Hint

**Semiconductor Theory Important MCQs with Hints**

**51). The concentration of electrons in N-type semiconductor is \_\_\_\_\_\_\_\_\_**

 Very high

 High

 Low

 Moderate

Hint

**52). The concentration of holes in P-type semiconductor is \_\_\_\_\_\_\_\_\_**

 Very high

 Very Low

 High

 Moderate

Hint

Read more about[P-type Semiconductor](https://www.watelectronics.com/p-type-semiconductor-explained/)

**53). How many valence electrons do trivalent impurities have?**

 One

 Two

 Three

 Four

Hint

**54). Germanium is an indirect bandgap semiconductor?**

 True

 False

Hint

**55). What is the unit of charge?**

 Voltmeter

 Ampere

 Coulombs

 None of the above

Hint

**56). The compound semiconductors are categorized into \_\_\_\_\_\_\_\_**

 One

 Two

 Three

 Four

Hint

**57). How many energy levels are possible in one atom?**

 Six

 Eight

 Three

 Seven

Hint

**58). The energy gap in insulators is \_\_\_\_\_\_\_**

 >3ev

 >2ev

 >4ev

 >5ev

Hint

**59). The concentration of holes in N-type semiconductor is \_\_\_\_\_\_\_\_\_**

 Less

 High

 Very high

 Moderate

Hint

Read more about [N-type Semiconductor](https://www.watelectronics.com/what-is-an-n-type-semiconductor/)

**60). The energy gap in semiconductors is \_\_\_\_\_\_\_**

 >3ev

 <3ev

 >4ev

 >5ev

Hint

**61). In \_\_\_\_\_\_\_\_ valence band is fully occupied and the conduction band is vacant**

 Insulators

 Conductors

 Both a and b

 None of the above

Hint

**62). In \_\_\_\_\_\_\_\_ both valence band and conduction band overlap each other**

 Insulators

 Conductors

 Metals

 Semiconductors

Hint

**63). What is the unit of conductivity?**

 Columbs

 Volts per meter

 Siemens/meter

 None of the above

Hint

**64). The aluminium gallium indium phosphide used for wavelengths between \_\_\_\_\_\_\_\_**

 500-900nm

 600-800nm

 560-650nm

 None of the above

Hint

**65). The bandgap in copper-zinc tin sulfide material is \_\_\_\_\_\_**

 0.9ev

 2ev

 5.6ev

 1.49ev

Hint

**66). The bandgap in copper-zinc antimony sulfide material is \_\_\_\_\_\_**

 2.2ev

 2ev

 5.6ev

 1.49ev

Hint

**67). The gallium arsenide used for \_\_\_\_**

 Fast electronics

 Near IR LEDs

 High-efficiency solar cells

 All of the above

Hint

**68). \_\_\_\_\_\_\_\_ material is used for ultraviolet LEDs**

 Boron arsenide

 Boron nitride

 Gallium phosphide

 None of the above

Hint

**69). The bandgap in boron nitride material is \_\_\_\_\_\_**

 2.2ev

 2ev

 6.36ev

 1.49ev

Hint

**70). \_\_\_\_\_\_\_\_\_\_ conducts electrical current easily**

 Conductor

 Semiconductor

 Insulator

 None of the above

Hint

**71). Which of the following has only one valence electron?**

 Conductor

 Semiconductor

 Insulator

 None of the above

Hint

**72). Which of the following has eight valence electrons?**

 Conductor

 Semiconductor

 Insulator

 None of the above

Hint

**73). The bandgap in boron arsenide material is \_\_\_\_\_\_**

 2.2ev

 1.14ev

 6.36ev

 1.49ev

Hint

**74). The resistance is very high in \_\_\_\_\_\_\_\_\_\_**

 Conductor

 Semiconductor

 Insulator

 None of the above

Hint

**75). The resistance is very small in \_\_\_\_\_\_\_\_\_\_**

 Conductor

 Semiconductor

 Insulator

 None of the above

Hint

**Semiconductor Theory Important MCQs for Quiz**

**76). Which of the following has a positive temperature coefficient?**

 Conductor

 Semiconductor

 Insulator

 None of the above

Hint

**77). Which of the following has a negative temperature coefficient?**

 Conductor

 Semiconductor

 Insulator

 Both b and c

Hint

**78). The bandgap in gallium phosphide material is \_\_\_\_\_\_**

 2.26ev

 1.14ev

 6.36ev

 1.49ev

Hint

**79). The relative conductivity of conductor is \_\_\_\_\_\_\_\_\_**

 Large

 Small

 Medium

Hint

**80). The relative resistance of conductor is \_\_\_\_\_\_\_\_\_**

 Large

 Small

 Medium

Hint

**81). The phosphorous impurity ionization energy in silicon is around\_\_\_\_\_\_\_\_**

 2.26ev

 0.045ev

 6.36ev

 1.49ev

Hint

**82). The bandgap in gallium arsenide material is around \_\_\_\_\_\_**

 2.26ev

 1.43ev

 6.36ev

 1.49ev

Hint

**83). The arsenic impurity ionization energy in silicon is around\_\_\_\_\_\_\_\_**

 2.26ev

 0.045ev

 0.05ev

 1.49ev

Hint

**84). The boron impurity ionization energy in germanium is around\_\_\_\_\_\_\_\_**

 2.26ev

 0.0104ev

 0.05ev

 1.49ev

Hint

**85). The aluminium impurity ionization energy in germanium is around\_\_\_\_\_\_\_\_**

 0.0102ev

 0.0104ev

 0.05ev

 1.49ev

Hint

**86). The relative conductivity of insulator \_\_\_\_\_\_\_\_\_**

 Small

 Large

 Medium

Hint

**87). The silicon material is \_\_\_\_\_\_\_**

 Cheap

 Ultra-high purity

 Both a and b

 None of the above

Hint

**88). The band gap in aluminum gallium arsenide is \_\_\_\_\_\_\_\_\_\_\_\_**

 0.0102ev

 0.0104ev

 0.05ev

 1.42ev

Hint

**89). The relative conductivity and relative resistivity of semiconductor both are \_\_\_\_\_\_\_\_**

 Small

 Large

 Medium

Hint

**90). The boron impurity ionization energy in silicon is around\_\_\_\_\_\_\_\_**

 0.0102ev

 0.0104ev

 0.045ev

 1.49ev

Hint

**91). The selenium impurity ionization energy in gallium arsenide is around\_\_\_\_\_\_\_\_**

 0.0102ev

 0.0059ev

 0.045ev

 1.49ev

Hint

**92). The tellurium impurity ionization energy in gallium arsenide is around\_\_\_\_\_\_\_\_**

 0.0102ev

 0.0058ev

 0.045ev

 1.49ev

Hint

**93). The beryllium impurity ionization energy in gallium arsenide is around\_\_\_\_\_\_\_\_**

 0.028ev

 0.0058ev

 0.045ev

 1.49ev

Hint

**94). The aluminium ionization energy in silicon is around\_\_\_\_\_\_\_\_**

 0.028ev

 0.0058ev

 0.06ev

 1.49ev

Hint

**95). The band gap in indium gallium arsenide is \_\_\_\_\_\_\_\_\_\_\_\_**

 0.36ev

 0.0104ev

 0.05ev

 1.42ev

Hint

**96). The phosphorous impurity ionization energy in germanium is around\_\_\_\_\_\_\_\_**

 0.028ev

 0.0058ev

 0.012ev

 1.49ev

Hint

**97). The zinc impurity ionization energy in gallium arsenide is around\_\_\_\_\_\_\_\_**

 0.028ev

 0.0058ev

 0.012ev

 0.0307ev

Hint

**98). The band gap in gallium phosphide material is \_\_\_\_\_\_\_\_\_\_\_\_**

 0.36ev

 0.0104ev

 1.35ev

 1.42ev

Hint

**99). The cadmium impurity ionization energy in gallium arsenide is around\_\_\_\_\_\_\_\_**

 0.028ev

 0.0058ev

 0.0347ev

 0.0307ev

Hint

**100). The germanium material has \_\_\_\_\_\_**

 High mobility

 High purity material

 Both a and b

 None of the above

Hint

**Semiconductor Theory Important MCQs for Exams**

**101). The arsenic impurity ionization energy in germanium is around\_\_\_\_\_\_\_\_**

 0.028ev

 0.0127ev

 0.0347ev

 0.0307ev

Hint

**102). The extrinsic semiconductor further classified into \_\_\_\_\_\_**

 One

 Two

 Three

 Four

Hint

**103). In which type of semiconductor electric density is greater than hole density?**

 N-type extrinsic semiconductor

 P-type extrinsic semiconductor

 Both a and b

 None of the above

Hint

**104). \_\_\_\_\_\_\_\_ is an example of semiconductor**

 Resistors

 Capacitors

 Op-amps

 All of the above

Hint

**105). Which one is a two-terminal semiconductor device?**

 Schottky diode

 FET

 IGBT

 None of the above

Hint

**106). Which one is a three-terminal semiconductor device?**

 Thyristor

 Solar cell

 LED

 None of the above

Hint

**107). In which type of semiconductor the hole density is greater than the electric density?**

 N-type extrinsic semiconductor

 P-type extrinsic semiconductor

 Both a and b

 None of the above

Hint

**108). What are the applications of semiconductor devices?**

 Microprocessors

 Analog circuits

 High voltage applications

 All of the above

Hint

**109). The power range of super junction MOSFET is \_\_\_\_\_\_\_\_\_**

 Up to 1KW

 Up to 5KW

 Up to 8KW

 Up to 10KW

Hint

**110). The power range of IGBT is \_\_\_\_\_\_\_\_\_**

 Up to 1Kw

 Up to 5Kw

 Several Mws

 Up to 10Kw

Hint

**111). The power range of Sic is \_\_\_\_\_\_\_\_\_**

 Up to 1Kw

 Up to 5Kw

 Several Mws

 Several 100’s Kw

Hint

**112). The power range of GaN is \_\_\_\_\_\_\_\_\_**

 Up to 1Kw

 Few Kw

 Several Mws

 Several 100’s Kw

Hint

**113). The thermal conductivity of silicon is \_\_\_\_\_\_\_\_**

 1w/cmk

 10w/cmk

 1.5w/cmk

 21w/cmk

Hint

**114). The band gap of silicon is \_\_\_\_\_\_\_\_\_**

 1ev

 2ev

 4ev

 1.11ev

Hint

**115). The breakdown field of silicon is \_\_\_\_\_\_\_\_**

 0.3MV/cm

 0.50MV/cm

 0.90MV/cm

 0.20MV/cm

Hint

**116). The semiconductor material silicon used in \_\_\_\_\_\_\_**

 Power amplifiers

 Mixed signal, MM-wave

 None of the above

Hint

**117). The semiconductor material gallium arsenide used in \_\_\_\_\_\_\_\_\_\_\_\_**

 ULSI, power amplifiers

 RF, microwave, MM wave

 Mixed-signal, MM-wave

 None of the above

Hint

**118). The semiconductor material silicon-germanium used in \_\_\_\_\_\_\_\_\_\_\_\_**

 Power amplifiers

 RF, microwave

 Mixed-signal, MM-wave, DSP

 Both b and c

Hint

**119). The semiconductor material GaN used in \_\_\_\_\_\_\_\_\_\_\_\_\_**

 Power amplifiers

 RF, microwave power amplifiers

 Mixed-signal, MM-wave, DSP

 Both b and c

Hint

**120). What is the standard form of AIP?**

 Aluminum Ionic Phosphide

 Aluminum Indium Phosphide

 Aluminum Phosphide

 None of the above

Hint

**121). What is the standard form of AIAS?**

 Aluminum Ionic Phosphide

 Aluminum Indium Arsenide

 Aluminum Arsenide

 None of the above

Hint

**122). The thermal conductivity of silicon carbide is \_\_\_\_\_\_\_\_**

 2.0w/cmk

 4.9w/cmk

 3.0w/cmk

 6.0w/cmk

Hint

**123). The breakdown field of silicon carbide is around \_\_\_\_\_\_\_\_\_\_**

 3.5mv/cm

 4.5mv/cm

 5.5mv/cm

 6.5mv/cm

Hint

**124). The band gap of silicon carbide is around \_\_\_\_\_\_\_\_\_\_**

 1ev

 2ev

 3.26ev

 4.5ev

Hint

**125). \_\_\_\_\_\_\_\_\_ are the compound semiconductors**

 Indium phosphide

 Aluminum phosphide

 Gallium phosphide

 All of the above

Hint

**Semiconductor Theory Important MCQs for Interviews**

**126). Which one is an elemental conductor?**

 Aluminum arsenide

 Gallium arsenide

 Germanium, silicon

 All of the above

Hint

**127). The Bohr model proposed in \_\_\_\_\_\_\_\_**

 1915

 2000

 2012

 2009

Hint

**128). Which one is a minority carrier device?**

 BJT

 PN diode

 JFET

 None of the above

Hint

**129). Which one is a majority carrier device?**

 Schottky diode

 Power MOSFET

 JFET

 All of the above

Hint

**130). The band gap of gallium nitride is around \_\_\_\_\_\_\_**

 1ev

 2ev

 3.39ev

 1.11ev

Hint

**131). The breakdown field of gallium nitride is \_\_\_\_\_\_\_\_**

 0.3MV/cm

 0.50MV/cm

 3.4MV/cm

 0.20MV/cm

Hint

**132). The thermal conductivity of gallium nitride is \_\_\_\_\_\_\_\_**

 1w/cmk

 10w/cmk

 1.5w/cmk

 2.0w/cmk

Hint

**133). The power semiconductor switching devices categorized into \_\_\_\_\_\_\_\_\_**

 One

 Two

 Three

 Four

Hint

**134). Which one is a photodetector?**

 Photothyristors

 TVS diodes

 Zener diodes

 None of the above

Hint

**135). Which one is a composite optical device?**

 Photo couplers

 Photo interrupters

 GaAs IC’s

 Both a and b

Hint

**136). \_\_\_\_\_\_\_\_ are the hybrid IC’s**

 GaAs

 MMICs

 Thin and thick membrane

 None of the above

Hint

**137). Which one is a light-emitting LED?**

 Switching diodes

 Zener diodes

 Laser diodes

 All of the above

Hint

**138). Which one is an analog IC?**

 Op-amps

 BUS switching

 CMOS logic IC’s

 All of the above

Hint

**139). Which one is a logic IC?**

 CMOS logic IC’s

 Bus switches

 General purpose logic IC’s

 All of the above

Hint

**140). The maximum frequency of IGBT is \_\_\_\_\_\_\_\_\_**

 10KHz

 40KHz

 60KHz

 80KHz

Hint

**141). The maximum frequency of MOSFET is \_\_\_\_\_\_\_\_\_**

 1MHz

 40KHz

 60KHz

 80KHz

Hint

**142). \_\_\_\_\_\_\_\_ elements have five valence electrons**

 P, sb, As, Bi

 Al, Ga

 B, In

 None of the above

Hint

**143). \_\_\_\_\_\_\_\_\_\_ type semiconductors are the semiconductors obtained by pentavalent impurity atoms**

 N-type semiconductors

 P-type semiconductors

 Both a and b

 None of the above

Hint

**144). \_\_\_\_\_\_\_\_\_\_ type semiconductors are the semiconductors obtained by trivalent impurity atoms**

 N-type semiconductors

 P-type semiconductors

 Both a and b

 None of the above

Hint

**145). Which one is an N-type semiconductor?**

 Arsenic

 Aluminum

 Gallium

 Boron

Hint

**146). Which one is a P-type semiconductor?**

 Arsenic

 Boron

 Phosphorous

 None of the above

Hint

**147). The depletion region depends on \_\_\_\_\_\_\_\_**

 Extent of doping

 Type of biasing

 Both a and b

 None of the above

Hint

**148). How many doping regions does the transistor have?**

 One

 Two

 Three

 Four

Hint

**149). Which one is a type of power diode?**

 Standard recovery diodes

 Silicon carbide diodes

 Schottky diodes

 Fast recovery diodes

 All of the above

Hint

Read more about [Diodes](https://www.watelectronics.com/types-of-diodes-applications/)

**150). The gains in common base amplifier and common emitter amplifier are \_\_\_\_\_\_**

 Current gain

 Voltage gain

 Power gain

 All of the above

Hint

**Semiconductor Theory Important MCQs for Engineers**

**151). In which type of semiconductor the conductivity an increases with increase in temperature?**

 Intrinsic

 Extrinsic

 Both a and b

 None of the above

Hint

**152). In an extrinsic semiconductor, the conductivity depends on the amount of impurity added?**

 True

 False

Hint

**153). The semiconductor doesn’t obey ohms law?**

 True

 False

Hint

**154). \_\_\_\_\_\_\_\_ is a most abundant carrier**

 Minority carriers

 Majority carriers

 Both a and b

 None of the above

Hint

**155). The silicon provides \_\_\_\_\_\_\_\_\_\_\_\_**

 High density

 Excellent energy resolution

 Excellent position resolution

 All of the above

Hint

**156). How many types of metal-semiconductor functions are there?**

 One

 Two

 Three

 Four

Hint

**157). \_\_\_\_\_\_\_\_ is a least abundant carrier**

 Minority carriers

 Majority carriers

 Both a and b

 None of the above

Hint

**158). The MESFET used in \_\_\_\_\_**

 Cellular phones

 Radars

 High-frequency devices

 All of the above

Hint

**159). The metal-semiconductor field-effect transistor fabricated in \_\_\_\_\_\_\_\_\_**

 Silicon

 GaAs

 Both a and b

 None of the above

Hint

**160). Based on geometry the carbon nano-tubes are \_\_\_\_\_\_\_\_**

 One

 Two

 Three

 Four

Hint

**161). Which diode is also known as hot barrier diode?**

 Schottky diode

 Photo diode

 Zener diode

 None of the above

Hint

**162). Which material is used to manufacture light depend on resistor?**

 Cadmium sulphide

 Cadmium selenide

 Lead sulphide

 All of the above

Hint

**163). How many types of GaAs devices are there?**

 One

 Two

 Three

 Four

Hint

**164). The advantages of tunnel diode are \_\_\_\_\_\_\_\_**

 High speed

 Low noise

 Low power

 All of the above

Hint

**165). The tunnel diode used in \_\_\_\_\_\_\_\_\_\_\_\_**

 Microwave oscillator

 Relaxation oscillator

 Logic memory storage devices

 All of the above

Hint

**166). \_\_\_\_\_\_\_\_\_\_ diode is also known as Eskai diode**

 Zener

 Photo

 Tunnel

 None of the above

Hint

**167). The varactor diode used in \_\_\_\_\_\_\_\_**

 AFC circuits

 TV receivers

 Used in FM radio

 All of the above

Hint